High Vol age, High C rren Darling on Transis or Arra s

The seven NPN Darlington connected transistors in these arrays are well suited for driving lamps, relays, or printer hammers in a variety of industrial and consumer applications. Their high breakdown voltage and internal suppression diodes insure freedom from problems associated with inductivej/F3377C1487sTn vtivrushTD0 8nsups, r1Fure fr TD00 mAc0.3897 Tw[1he seven N, 200(permit)Tjmfr

MAXIMUM RATINGS ($T_A = 25^{\circ}C$, and rating apply to any one device in the package, unless otherwise noted.)

Rating	Symbol	Value	Unit
Output Voltage	Vo	50	V
Input Voltage	VI	30	V
Collector Current – Continuous	I _C	500	mA
Base Current – Continuous	Ι _Β	25	mA
Operating Ambient Temperature Range MC1413 MC1413B NCV1413B	T _A	-20 to +85 -40 to +85 -40 to +125	ů
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	TJ	150	°C
Thermal Resistance, Junction-to-Ambient Case 648, P Suffix Case 751B, D Suffix	$R_{ heta JA}$	67 100	°C/W
Thermal Resistance, Junction-to-Case Case 648, P Suffix Case 751B, D Suffix	$R_{ heta JC}$	22 20	°C/W
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM) Charged Device Model (CDM)	ESD	2000 400 1500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Leakage Current $ (V_O = 50 \text{ V}, T_A = +85^{\circ}\text{C}) $ All Type $ (V_O = 50 \text{ V}, T_A = +25^{\circ}\text{C}) $ All Type		- -	- -	100 50	μΑ
$\label{eq:collector-Emitter Saturation Voltage} \tag{$I_C=350$ mA, $I_B=500$ μA}) & \text{All Type} \\ (I_C=200$ mA, $I_B=350$ μA}) & \text{All Type} \\ (I_C=100$ mA, $I_B=250$ μA}) & \text{All Type} \\ \end{aligned}$	s	- - -	1.1 0.95 0.85	1.6 1.3 1.1	V
Input Current – On Condition (V _I = 3.85 V) MC1413,	I _{I(on)}	-	0.93	1.35	mA
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	В	- - -	- - -	2.4 2.7 3.0	V
Input Current – Off Condition All Type $(I_C = 500 \ \mu A, T_A = 85^{\circ}C)$	s I _{I(off)}	50	100	_	μΑ
DC Current Gain ($V_{CE} = 2.0 \text{ V}, I_{C} = 350 \text{ mA}$)	h _{FE}	1000	_	_	-
Input Capacitance	C _I	-	15	30	pF
Turn-On Delay Time (50% E _I to 50% E _O)	t _{on}	-	0.25	1.0	μs
Turn–Off Delay Time (50% E _I to 50% E _O)	t _{off}	-	0.25	1.0	μs
Clamp Diode Leakage Current $T_A = +25^{\circ}$ $(V_R = 50 \text{ V})$ $T_A = +85^{\circ}$		_ _	- -	50 100	μΑ
Clamp Diode Forward Voltage (I _F = 350 mA)	V _F	-	1.5	2.0	V

NOTE: NCV1413B T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

TYPICAL PERFORMANCE CURVES - T_A = 25°C

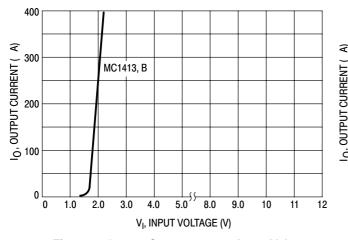
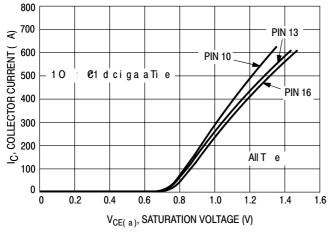


Figure 3. Output Current versus Input Voltage

Figure 4. Output Current versus Input Current



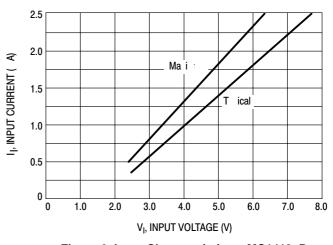


Figure 5. Typical Output Characteristics

Figure 6. Input Characteristics - MC1413, B

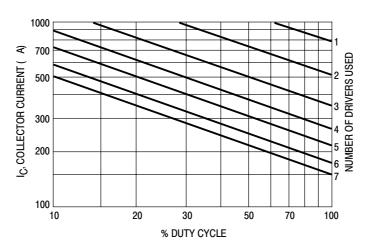
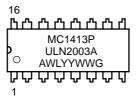
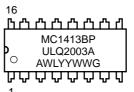


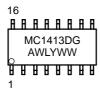
Figure 7. Maximum Collector Current versus Duty Cycle (and Number of Drivers in Use)

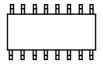
MARKING DIAGRAMS

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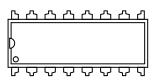


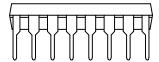




PDIP-16 CASE 648-08 ISSUE V

DATE 22 APR 2015





STYLE 1:

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 YY = Year
 WW = Work Week
 G = Pb-Free Package

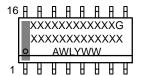
^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " •", may or may not be present.

SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

SOIC-16 9.90x3.90x1.50 1.27PCASE 751B ISSUE L

DATE 29 MAY 2024

GENERIC MARKING DIAGRAM*

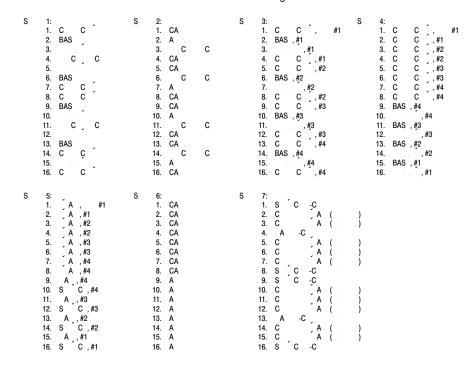


XXXXX = Specific Device Code

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



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